

V _{CES}	650V
I _{C (100°C)}	30A
V _{CE(sat) (Typ.)}	1.5V
P _D	178W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

PFC

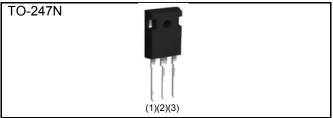
UPS

Welding

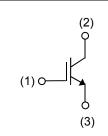
Solar Inverter

IH

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tupo	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGW60TS65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C}$ = 25°C	Ι _C	60	А
Collector Current	T _C = 100°C	r _c = 100°C I _c		А
Pulsed Collector Current		I _{CP} *1	120	А
$T_{\rm C} = 25^{\circ}{\rm C}$		P _D	178	W
Power Dissipation	T _C = 100°C	P _D	89	W
Operating Junction Temperature		Тj	-40 to +175	°C
Storage Temperature		T _{stg}	–55 to +175	°C

*1 Pulse width limited by T_{jmax}.

•Thermal Resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	R _{θ(j-c)}	-	-	0.84	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Linit
Farameter	Symbol Conditions -		Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 20.0mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 30A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.5 1.85	1.9 -	V

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Demonster	Cyrob el					
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2530	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	65	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	46	-	
Total Gate Charge	Qg	V _{CE} = 400V	-	84	-	
Gate - Emitter Charge	Q_{ge}	I _C = 30A	-	17	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	31	-	
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	37	-	
Rise Time	t _r	V_{GE} = 15V, R_G = 10 Ω	-	13	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	114	-	ns
Fall Time	t _f	Inductive Load	-	35	-	
Turn - on Switching Loss	E_{on}	*E _{on} includes diode	-	0.48	-	mJ
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.49	-	IIIJ
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	36	-	
Rise Time	t _r	V_{GE} = 15V, R_{G} = 10 Ω	-	14	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	133	-	ns
Fall Time	t _f	Inductive Load	-	76	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.49	-	m
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.63	-	mJ
		I _C = 120A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	V _P = 650V, V _{GE} = 15V	FU	LL SQUA	RE	-
		R _G = 100Ω, T _j = 175°C				

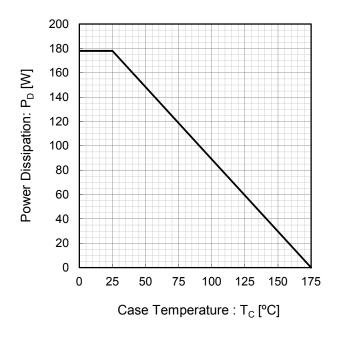


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

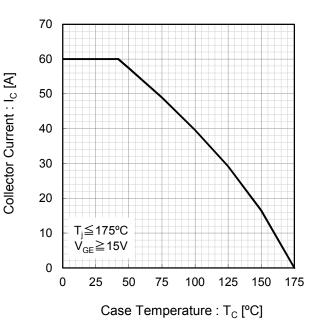
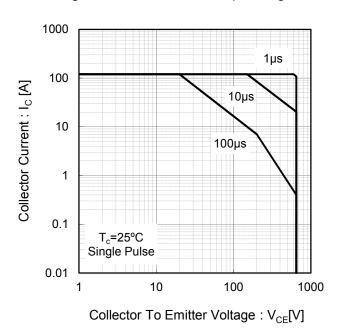
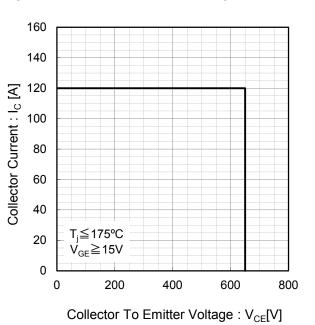


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area





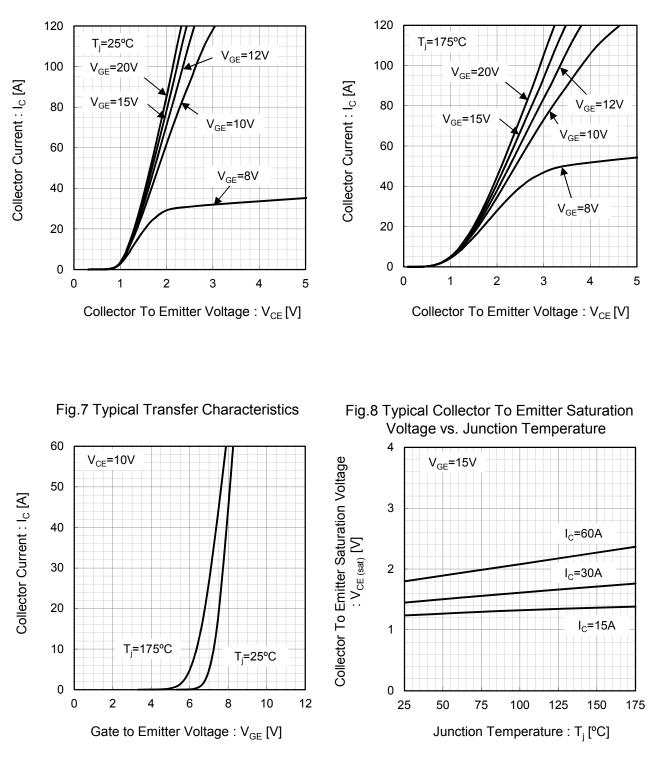
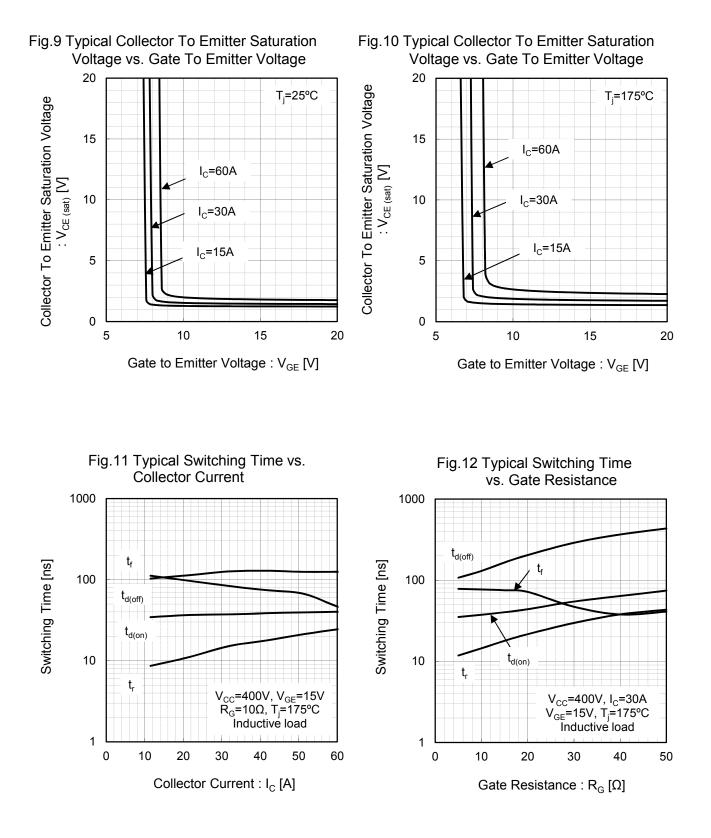
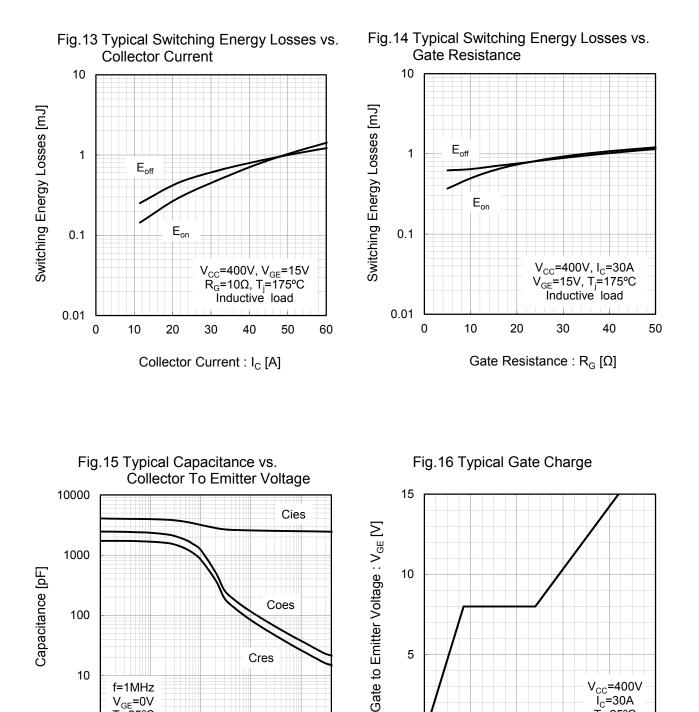


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics





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25°C

0.1

1

Collector To Emitter Voltage : $V_{CE}[V]$

10

100

1

0.01

T_i=25°C

80

100

0

0

20

40

60

Gate Charge : Q_q[nC]

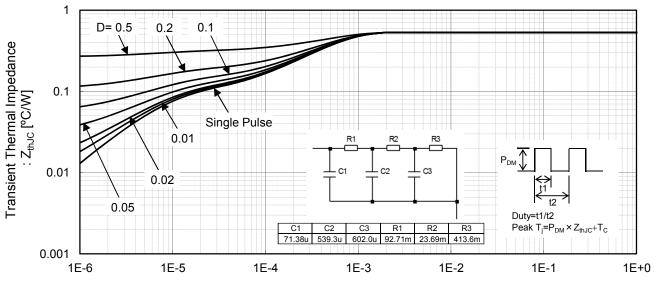
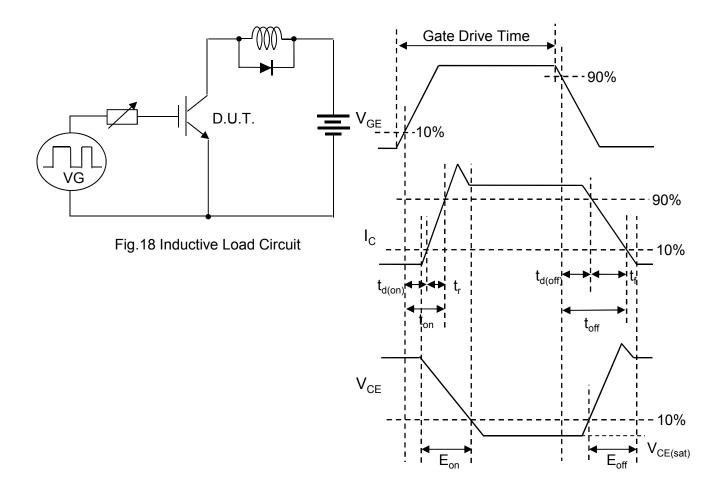
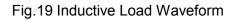


Fig.17 Typical IGBT Transient Thermal Impedance

Pulse Width : t1[s]

Inductive Load Switching Circuit and Waveform





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